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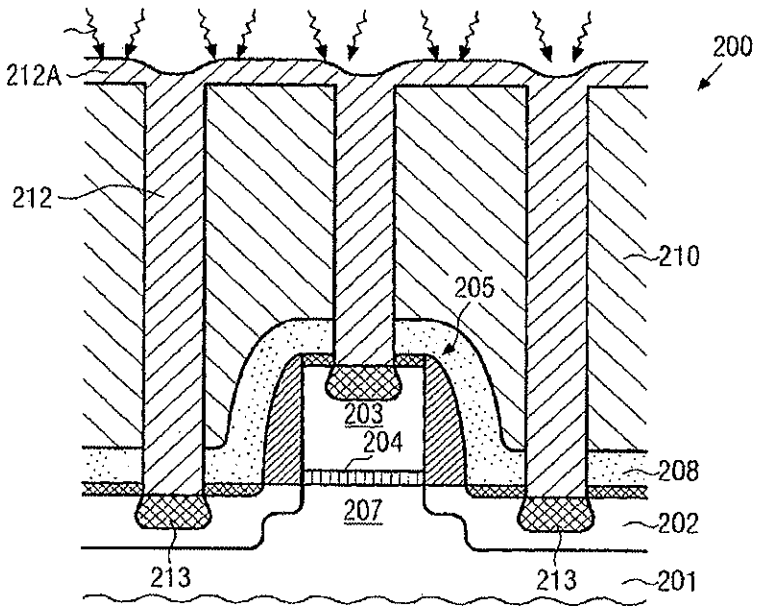
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(54) Title: A TRANSISTOR HAVING A LOCALLY PROVIDED METAL SILICIDE REGION IN CONTACT AREAS AND A METHOD OF FORMING THE TRANSISTOR



(57) Abstract: By performing a silicidation process on the basis of a patterned dielectric layer, such as an interlayer dielectric material, the respective metal silicide portions may be provided in a highly localized manner at the respective contact regions, while the overall amount of metal silicide may be significantly reduced. In this way, a negative influence of the stress of metal silicide on the channel regions of field effect transistors may be significantly reduced, while nevertheless maintaining a low contact resistance.

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